

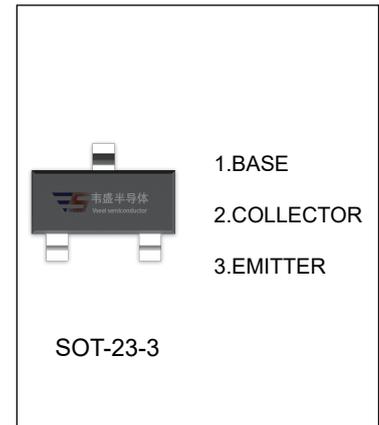
VS201NL TRANSISTOR (NPN)

FEATURES

- High Collector Current Capability
- Low Collector-emitter Saturation Voltage
- High Efficiency Leading to Less Heat Generation
- Reduced PCB Requirements
- Alternated Effectively to MOSFETS in Specific Applications

APPLICATIONS

- Power Management
- Peripheral Driver


MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	20	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	1	A
P _C	Collector Power Dissipation	300	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	417	°C/W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	I _{CB0}	V _{CB} =30V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =2V, I _C =100mA	350			
	h _{FE(2)}	V _{CE} =2V, I _C =500mA	300			
	h _{FE(3)}	V _{CE} =2V, I _C =1A	280			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =100mA, I _B =1mA			80	mV
	V _{CE(sat)2}	I _C =500mA, I _B =50mA			110	mV
	V _{CE(sat)3}	I _C =750mA, I _B =15mA			200	mV
	V _{CE(sat)4} *	I _C =1A, I _B =50mA			250	mV
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =1A, I _B =100mA			1.1	V
Base-emitter turn-on voltage	V _{BE(on)}	V _{CE} =2V, I _C =100mA			0.75	V
Transition frequency	f _T	V _{CE} =10V, I _C =100mA, f=100MHz	100			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			20	pF

*Pulse test: pulse width ≤300μs, duty cycles ≤2.0%.